

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(on)} Max	Package	I _D Max T _A = +25°C
-20V	$52m\Omega @V_{GS} = -4.5V$	SOT23	-5.0A
-20V	100mΩ @V _{GS} = -2.5V	30123	-3.6A

Description

This MOSFET is designed to minimize on-state resistance (R_{DS(on)}), yet maintain superior switching performance, making it ideal for highefficiency power management applications.

Applications

- Backlighting
- **Power Management Functions**
- DC-DC Converters
- Motor Controls

Features

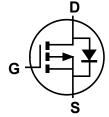
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMG2305UXQ)

Mechanical Data

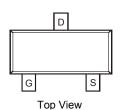
- Case: SOT23 (Standard)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)







Internal Schematic



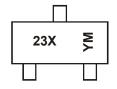
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMG2305UX-7	Standard	SOT23 (Standard)	3,000/Tape & Reel
DMG2305UX-13	Standard	SOT23 (Standard)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain < 900ppm bromine, < 900ppm chlorine (< 1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



23X = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Key

Year	2009		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	W		I	J	K	L	М	N	0	Р	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
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Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-20	V	
Gate-Source Voltage	V _{GSS}	±8	V		
Continuous Prain Current (Note EVV - 4 EV	Steady State	T _A = +25°C T _A = +70°C	I _D	-4.2 -3.3	А
Continuous Drain Current (Note 5) V _{GS} = -4.5V	t<10s	T _A = +25°C T _A = +70°C	I _D	-5.0 -4.0	А
Pulsed Drain Current (10μs Pulse, Duty Cycle =	1%) (Note	: 6)	I _{DM}	-15	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 5)		P_D	1.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	90	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{ heta JA}$	64	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	33	°C/W	
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

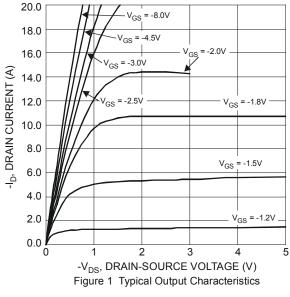
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

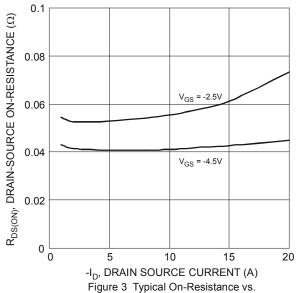
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V$, $I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	_	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			40	52		$V_{GS} = -4.5V$, $I_D = -4.2A$
Static Drain-Source On-Resistance	R _{DS(on)}	_	52	100	mΩ	V _{GS} = -2.5V, I _D = -3.4A
			68	200		V _{GS} = -1.8V, I _D = -2A
Forward Transfer Admittance	Y _{FS}	_	9	_	s	$V_{DS} = -5V, I_{D} = -4A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}		808		pF	
Output Capacitance	Coss		85		pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	77	_	pF	1.01/11/2
Gate Resistance	Rg		15.2		Ω	V _{GS} = 0V, V _{DS} = 0V, f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Qg		10.2		nC	V 45V V 4V
Gate-Source Charge	Q_{gs}	_	1.3		nC	V_{GS} = -4.5V, V_{DS} = -4V, I_{D} = -3.5A
Gate-Drain Charge	Q_{gd}	_	2.2	_	nC	1D = -3.5A
Turn-On Delay Time	t _{D(on)}	_	10.8	_	ns	
Turn-On Rise Time	t _R	_	13.7	_	ns	V _{DS} = -4V, V _{GS} = -4.5V,
Turn-Off Delay Time	t _{D(off)}	_	79.3	_	ns	$R_g = 6\Omega$, $I_D = -1A$
ırn-Off Fall Time t _i		_	34.7	_	ns]

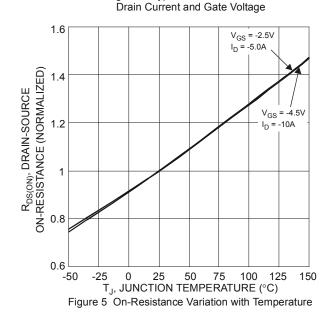
Notes:

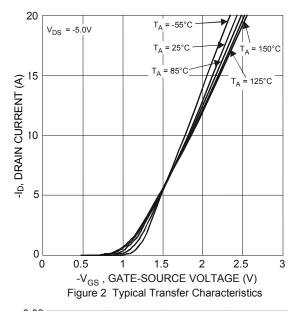
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

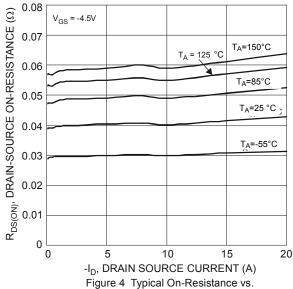












Drain Current and Temperature

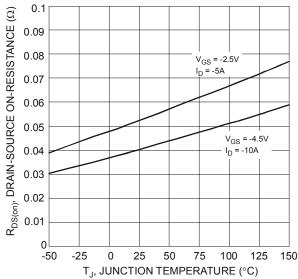


Figure 6 On-Resistance Variation with Temperature



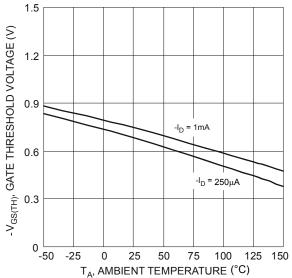
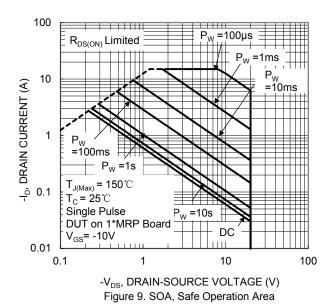


Figure 7 Gate Threshold Variation vs. Ambient Temperature



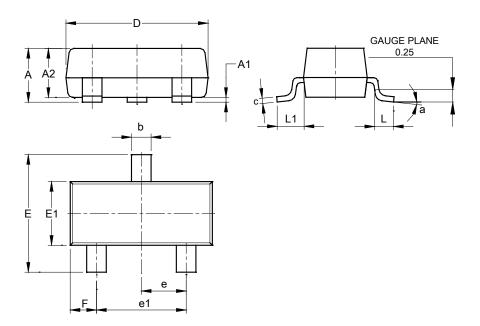
20 18 16 -I_S, SOURCE CURRENT (A) 12 10 T_A= 25°C 6 2 0 0 0.3 0.6 0.9 1.2 1.5 $-V_{SD}$, SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)

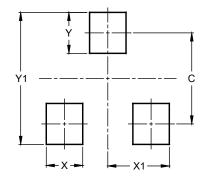


S	SOT23 (Standard)							
Dim	Min	Max	Тур					
Α	0.90	1.15	1.025					
A1	0.00	0.10	0.05					
A2	0.85	1.10	0.975					
b	0.30	0.51	0.40					
С	0.080	0.202	0.11					
D	2.80	3.00	2.90					
Е	2.25	2.55	2.40					
E1	1.20	1.40	1.30					
е	0.89	1.03	0.915					
e1	1.78	2.05	1.83					
F	0.40	0.60	0.535					
L1	0.45	0.61	0.55					
٦	0.25	0.55	0.40					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)			
С	2.0			
Х	0.8			
X1	1.35			
Υ	0.9			
V4	2.0			



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